

CLAIMS:

1. A silicon oxide powder represented by the formula:  
SiO<sub>x</sub> wherein x is from 1.05 to 1.5 and having a BET specific  
surface area of 5 to 300 m<sup>2</sup>/g.
2. A method for preparing the silicon oxide powder of  
claim 1, comprising the steps of:  
heating a raw material powder mixture containing at  
least a silicon dioxide powder in an inert gas atmosphere or  
in vacuum at a temperature of 1,100 to 1,600°C to generate  
SiO gas,  
continuously or intermittently feeding oxygen gas to  
the SiO gas to form a gas mixture, and  
depositing the gas mixture on a surface of a cooled  
substrate.
3. The method of claim 2 wherein the depositing step  
includes cooling the substrate surface at a temperature of  
200 to 400°C.